



2SA733

PNP SILICON TRANSISTOR

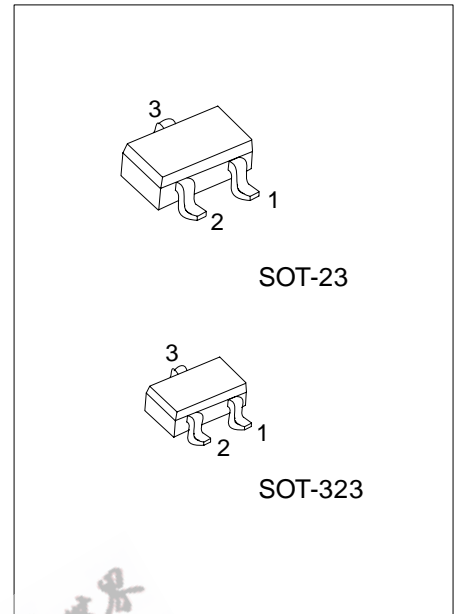
LOW FREQUENCY AMPLIFIER PNP EPITAXIAL SILICON TRANSISTOR

DESCRIPTION

The UTC **2SA733** is a low frequency amplifier.

FEATURES

- * Collector-Emitter voltage:
BV_{CBO}=-50V
- * Collector current up to -150mA
- * High h_{FE} linearity
- * Complimentary to 2SC945



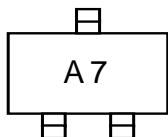
*Pb-free plating product number:2SA733L

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SA733-x-AE3-R	2SA733L-x-AE3-R	SOT-23	E	C	B	Tape Reel
2SA733-x-AL3-R	2SA733L-x-AL3-R	SOT-323	E	C	B	Tape Reel

<p>2SA733L-x-AE3-R</p>	<p>(1) Packing Type (2) Package Type (3) Rank (4) Lead Plating</p> <p>(1) R: Tape Reel (2) AE3: SOT-23, AL3: SOT-323 (3) x: refer to Classification of h_{FE} (4) L: Lead Free Plating, Blank: Pb/Sn</p>
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MARKING



■ ABSOLUTE MAXIMUM RATING (Ta=25 , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Dissipation(Ta=25)	P _C	250	mW
Collector Current	I _C	-150	mA
Junction Temperature	T _J	125	
Storage Temperature	T _{STG}	-55 ~ +150	

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25 , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA, I _E =0	-60			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-10mA, I _B =0	-50			V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-100mA, I _B =-10mA		-0.1	-0.3	V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-40V, I _E =0			-100	nA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-3V, I _C =0			-100	nA
DC Current Gain(note)	h _{FE}	V _{CE} =-6V, I _C =-1mA	90		600	
Current Gain Bandwidth Product	f _T	V _{CE} =-10V, I _C =-50mA	100	190		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		2.0	3.0	pF
Noise Figure	NF	I _C =-0.1mA, V _{CE} =-6V R _G =10kΩ, f=100Hz		4.0	6.0	dB

■ CLASSIFICATION OF h_{FE}

RANK	R	Q	P	K
RANGE	90-180	135-270	200-400	300-600

TYPICAL CHARACTERISTICS

Fig.1 Static Characteristics

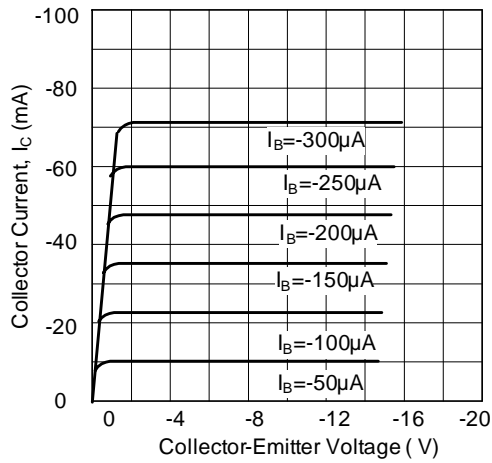


Fig.2 DC Current Gain

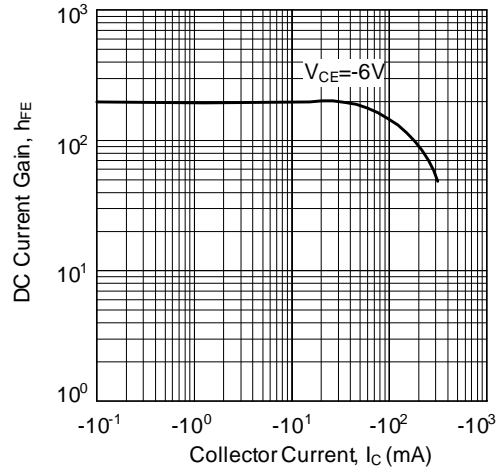


Fig.3 Base-Emitter on Voltage

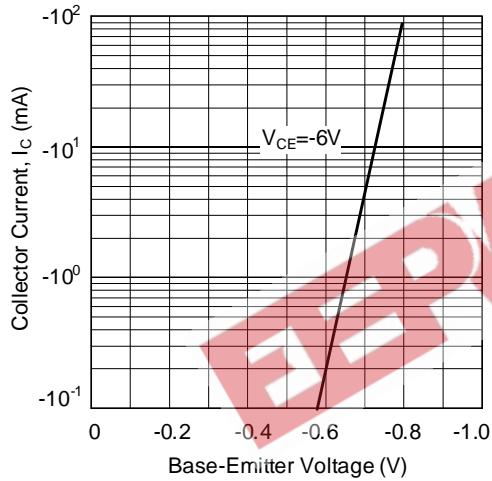


Fig.4 Saturation Voltage

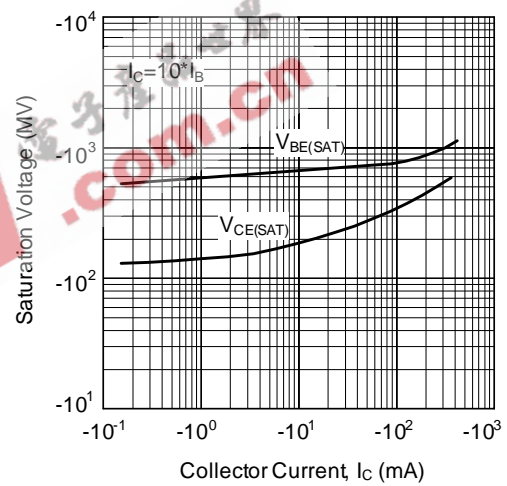


Fig.5 Current Gain-Bandwidth Product

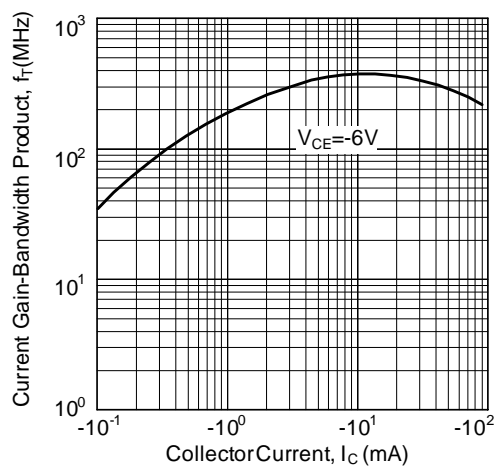
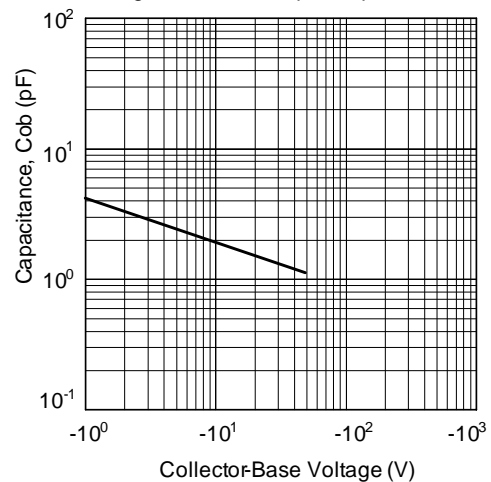


Fig.6 Collector Output Capacitance



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